

Figure 2. Logic Diagram

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	-0.5 to +7.0	V
V _{IN}	DC Input Voltage (Referenced to GND)	-0.5 to V_{CC} +0.5	V
V _{OUT}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} +0.5	V
I _{IN}	DC Input Current, per Pin	±20	mA
I _{OUT}	DC Output Current, per Pin	±50	mA
I _{CC}	DC V _{CC} or GND Current per Output Pin	±50	mA
P _D	Power Dissipation in Still Air Plastic† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	-65 to +150	°C
T _L	Lead Temperature, 1 mm from Case for 10 seconds (Plastic DIP or SOIC Package)	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{IN} /V _{OUT}	Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	_
T _A	Operating Temperature, All Package Types	-40	+85	°C
t _r /t _f	Input Rise/Fall Time $V_{CC} = 3.0 \text{ V}$ (Figure 1) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 5.5 \text{ V}$	0 0 0	150 40 25	ns/V

[†]Derating: Plastic DIP: - 10mW/°C from 65°C to 125°C SOIC Package: -7.0 mW/°C from 65°C to 125°C

DC CHARACTERISTICS (unless otherwise specified)

Symbol	Parameter	Value	Unit	
I _{CC}	Maximum Quiescent Supply Voltage	80	μΑ	$V_{in} = V_{CC}$ or GND $V_{CC} = 5.5 \text{ V}, T_A = \text{Worst Case}$
I _{CC}	Maximum Quiescent Supply Current		μΑ	$V_{\text{in}} = V_{\text{CC}} \text{ or GND}$ $V_{\text{CC}} = 5.5 \text{ V}, T_{\text{A}} = 25^{\circ}\text{C}$

DC CHARACTERISTICS

			74AC 74AC				
		V _{CC}	T _A = -	-25°C	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$		
Symbol	Parameter	(V)	Тур	G	uaranteed Limits	Unit	Conditions
V _{IH}	Minimum High Level Input Voltage	3.0 4.5 5.5		2.1 3.15 3.85	2.1 3.15 3.85	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{IL}	Maximum Low Level Input Voltage	3.0 4.5 5.5	- - -	0.9 1.35 1.65	0.9 1.35 1.65	V	V _{OUT} = 0.1 V or V _{CC} – 0.1 V
V _{OH}	Minimum High Level Output Voltage	3.0 4.5 5.5	2.99 4.49 5.49	2.9 4.4 5.4	2.9 4.4 5.4	V	I _{OUT} = -50 μA
		3.0 4.5 5.5		2.56 3.86 4.86	2.46 3.76 4.76	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ -12 mA I_{OH} -24 mA -24 mA
V _{OL}	Maximum Low Level Output Voltage	3.0 4.5 5.5	0.002 0.001 0.001	0.1 0.1 0.1	0.1 0.1 0.1	V	Ι _{ΟUT} = 50 μΑ
		3.0 4.5 5.5	- - -	0.36 0.36 0.36	0.44 0.44 0.44	V	$^*V_{IN} = V_{IL} \text{ or } V_{IH}$ 12 mA I_{OL} 24 mA 24 mA
I _{IN}	Maximum Input Leakage Current	5.5	-	±0.1	±1.0	μΑ	V _I = V _{CC} , GND
I _{OLD}	Minimum Dynamic Output Current†	5.5	-	-	75	mA	V _{OLD} = 1.65 V Max
I _{OHD}		5.5	-	-	- 75	mA	V _{OHD} = 3.85 V Min

 $^{^{\}star}\text{All}$ outputs loaded; thresholds on input associated with output under test. †Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS (For Figures and Waveforms - See Section 3 of the ON Semiconductor FACT Data Book, DL138/D)

			74AC		74AC				
		V _{CC} *	T _A = +25°C C _L = 50 pF		$T_A = -40^{\circ}\text{C to } +85^{\circ}\text{C}$ $C_L = 50 \text{ pF}$				
Symbol	Parameter	(V)	Min	Тур	Max	Min	Max	Unit	Fig. No.
f _{max}	Maximum Clock Frequency	3.3 5.0	110 130	120 140	-	100 120	-	MHz	-
n _{CP} to Q1	Propagation Delay n _{CP} to Q1	3.3 5.0	2.0 2.0	-	11 8.0	2.0 2.0	14 10	ns	-
Q _n to Q _n +1	Propagation Delay Q _n to Q _n +1	3.3 5.0	0 0		5.5 3.5	0 0	6.5 4.5	ns	-
MR to Q t _{HL}	Propagation Delay MR to Q	3.3 5.0	3.0 3.0		12 10	3.0 3.0	15 12	ns	-
t _{rec} n _{CP} to MR	Recovery Time	3.3 5.0	0 0	-2.5 -1.5	-	0 0	-	ns	-
t _w n _{CP}	Minimum Pulse Width Clock Pin	3.3 5.0	4.0 3.0	3.5 2.5	_ _	4.5 3.5		ns	-
t _w MR	Minimum Pulse Width Master Reset	3.3 3.0	4.0 3.0	3.5 2.5	- -	4.5 3.5	-	ns	_

^{*}Voltage Range 3.3 V is 3.3 V ± 0.3 V.

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C _{IN}	Input Capacitance	4.5	pF	V _{CC} = 5.0 V
C _{PD}	Power Dissipation Capacitance	50	pF	V _{CC} = 5.0 V

MARKING DIAGRAMS

PDIP-16

 SOIC-16

AC4040G AWLYWW SOEIAJ-16

74AC4040 ALYW

A = Assembly Location

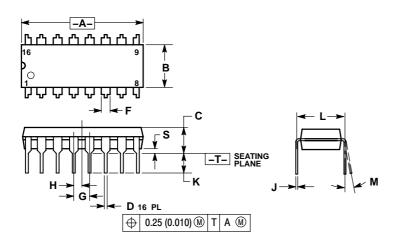
WL, L = Wafer Lot YY, Y = Year WW, W = Work Week

G = Pb-Free Package

^{*}Voltage Range 5.0 V is 5.0 V ±0.5 V.

PACKAGE DIMENSIONS

PDIP-16 CASE 648-08 **ISSUE T**



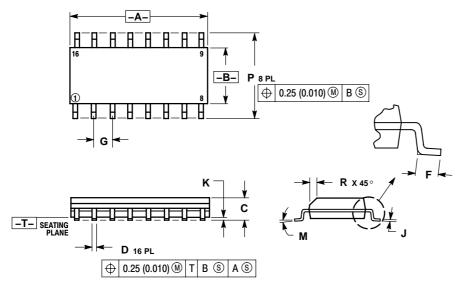
STYLE 2: PIN 1. 2. STYLE 1: PIN 1. COMMON DRAIN CATHODE CATHODE CATHODE COMMON DRAIN COMMON DRAIN 3. 4. 5. 3 CATHODE COMMON DRAIN CATHODE CATHODE CATHODE COMMON DRAIN 6. 7. 6. 7. 8. 9. 10. 11. COMMON DRAIN COMMON DRAIN COMMON DRAIN GATE SOURCE CATHODE ANODE ANODE 9. 10. 11. ANODE GATE 12. SOURCE 13. GATE 12. ANODE ANODE 13. 14. ANODE 14. SOURCE 15. ANODE 15. GATE 16. SOURCE

NOTES:

- DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEADS
 WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
- ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS		
DIM	MIN	MAX	MIN	MAX		
Α	0.740	0.770	18.80	19.55		
В	0.250	0.270	6.35	6.85		
С	0.145	0.175	3.69	4.44		
D	0.015	0.021	0.39	0.53		
F	0.040	0.70	1.02	1.77		
G	0.100	BSC	2.54	BSC		
Н	0.050	BSC	1.27	BSC		
J	0.008	0.015	0.21	0.38		
K	0.110	0.130	2.80	3.30		
L	0.295	0.305	7.50	7.74		
М	0°	10 °	0 °	10 °		
S	0.020	0.040	0.51	1.01		

SOIC CASE 751B-05 **ISSUE J**



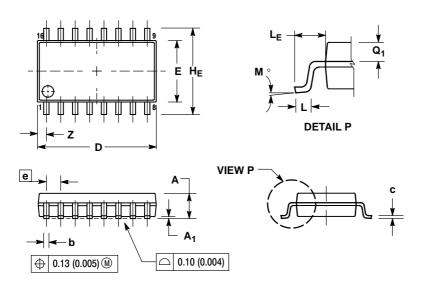
16. ANODE

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
P	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS

SOEIAJ-16 CASE 966-01 **ISSUE A**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 - CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
 THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION.
 DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050	BSC
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
Q_1	0.70	0.90	0.028	0.035
Z		0.78		0.031

ON Semiconductor and un are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice on semiconductor and are registered readerlands of semiconductor Components industries, Ltc (SciLLC). Solitude services the inject to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications. intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada

Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

MC74AC4040/D